

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

www.centrasemi.com

2N3467

2N3468

PNP SILICON TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3467, 2N3468 types are Silicon PNP Switching Transistors designed for core driver applications

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	2N3467	2N3468	UNIT
Collector-Base Voltage	V _{CBO}	40	50	V
Collector-Emitter Voltage	V _{CEO}	40	50	V
Emitter-Base Voltage	V _{EBO}	5.0		V
Collector Current	I _C	1.0		A
Power Dissipation	P _D	1.0		W
Power Dissipation (T _C =25°C)	P _D	5.0		W
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +200		°C
Thermal Resistance	θ _{JA}	175		°C/W
Thermal Resistance	θ _{JC}	35		°C/W

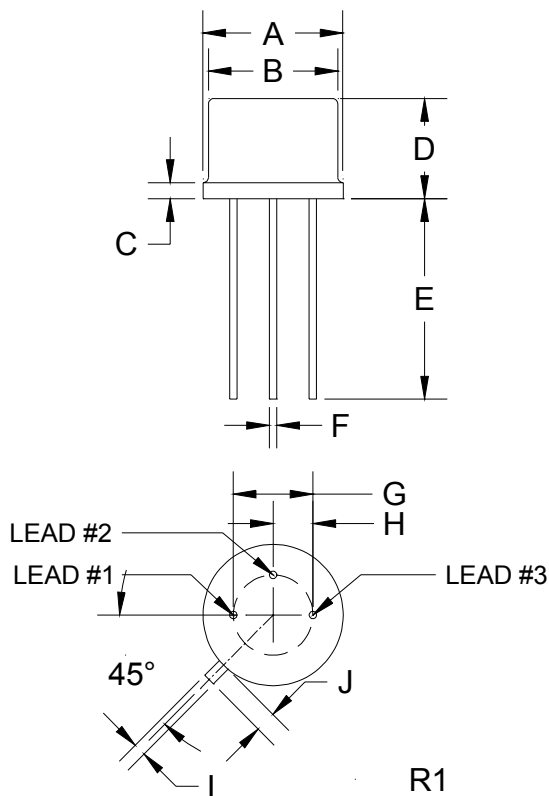
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3467		2N3468		UNIT
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =30V		0.1		0.1	μA
I _{CBO}	V _{CB} =30V, T _A =100°C		15		15	μA
I _{CEV}	V _{CE} =30V, V _{BE} =3.0V		100		100	nA
I _{BEV}	V _{CE} =30V, V _{BE} =3.0V		120		120	nA
BV _{CBO}	I _C =10μA	40		50		V
BV _{CEO}	I _C =10mA	40		50		V
BV _{EBO}	I _E =10μA	5.0		5.0		V
V _{CE} (SAT)	I _C =150mA, I _B =15mA		0.3		0.36	V
V _{CE} (SAT)	I _C =500mA, I _B =50mA		0.5		0.6	V
V _{CE} (SAT)	I _C =1.0A, I _B =100mA		1.0		1.2	V
V _{BE} (SAT)	I _C =150mA, I _B =15mA		1.0		1.0	V
V _{BE} (SAT)	I _C =500mA, I _B =50mA	0.8	1.2	0.8	1.2	V
V _{BE} (SAT)	I _C =1.0A, I _B =100mA		1.6		1.6	V

(SEE REVERSE SIDE)

ELECTRICAL CHARACTERISTICS (Continued)

SYMBOL	TEST CONDITIONS	2N3467		2N3468		UNITS
		MIN	MAX	MIN	MAX	
h_{FE}	$V_{CE}=1.0V, I_C=150mA$	40		25		
h_{FE}	$V_{CE}=1.0V, I_C=500mA$	40	120	25	75	
h_{FE}	$V_{CE}=5.0V, I_C=1.0A$	40		20		
f_T	$V_{CE}=10V, I_C=50mA, f=100MHz$	175		150		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=100kHz$		25		25	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=100kHz$		100		100	pF
t_{ON}	$V_{CC}=30V, V_{BE}=2.0V, I_C=500mA, I_{B1}=50mA$		40		40	ns
t_{OFF}	$V_{CC}=30V, I_C=500mA, I_{B1}=I_{B2}=50mA$		90		90	ns
QT	$V_{CC}=30V, I_C=500mA, I_B=50mA$		6.0		6.0	nC

TO-39 CASE - MECHANICAL DIMENSIONS

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

Lead Code:

- 1) Emitter
- 2) Base
- 3) Collector

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